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Atlanta, GA 30332-0100, USA
Telefax: +1-404-894 2866

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Room 1A-363, AT&T Bell Laboratories
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Telefax: +1-908-582 2521

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B-2020 Antwerp, Belgium
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Dept. of Metallurgy & Materials Science
Massachusetts Institute of Technology
Cambridge, MA 02139, USA
Telefax: +1-617-253 5827

Editor International Organization for Crystal Growth (IOCG) News:
B. COCKAYNE, DRA Malvern, St. Andrews Road, Great Malvern, Worcs. WR14 3PS, UK, Telefax: +44-684-894 540

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Chastaingt, B., C. Deparis, G. Neu, M. Leroux, N. Grandjean and J. Massies, Growth of ultra-thin AlAs layers on GaAs (001) vicinal surfaces: a search for lateral confinement 127 (1993) 831
Chatillon, C., Critical analysis of the thermodynamic properties of the In–Se gaseous and solid phases 129 (1993) 297
Chatillon, C. and J.-Y. Emery, Thermodynamic analysis of molecular beam epitaxy of compounds in the In–Se system 129 (1993) 312
Chatillon, C., J.C. Harmand and F. Alexandre, Thermodynamic analysis of GaAs growth by molecular beam epitaxy at the surface structure transition from 3×1 to 4×2 130 (1993) 451
Chaussavoine, C., see Wang 126 (1993) 373
Chayen, N.E., P.D. Shaw Stewart and D.M. Blow, Microbatch crystallization under oil – a new technique allowing many small-volume crystallization trials 122 (1992) 176
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Chen, A.C., see Pearah 127 (1993) 900
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Chen, C.H., C.T. Chiu, G.B. Stringfellow and R.W. Gedridge, Jr., Triisopropylindium for OMVPE growth 124 (1992) 88
Chen, C.H., K.T. Huang, D.L. Drobeck and G.B. Stringfellow, Tertiarybutyldimethylantimony for InSb growth 124 (1992) 142
Chen, C.H., G.B. Stringfellow and R.W. Gedridge, Jr., Triisopropylindium: decomposition study and use for low temperature growth of InAs 126 (1993) 309
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Chen, H.S., see Kortan 128 (1993) 1086
Chen, J.C., see Fernández 127 (1993) 570
Chen, L.J., C.C. Wan and C. Lien, Simulation of the growth rate and layer thickness for liquid phase epitaxy (LPE) under slider-induced convection 121 (1992) 322
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Chen, Nuofu, Ultrasonic etching of GaAs in CrO_3–HF aqueous solutions 129 (1993) 777
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Chen, P.C., C.Y. Tai and S.M. Shih, Control of crystal habit and particle morphology of calcium sulfite hemihydrate crystals 123 (1992) 277
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Cherenkov, A., see Dmitriev 128 (1993) 343
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and K. Tsukamoto, Advance velocities of steps on {211} and {110} faces of yttrium iron garnet: theory and observations 121 (1992) 1
Cherepanova, T.A., P. Bennema, Yu.A. Yanson and L.J.P. Vogels, Morphology of synthetic and natural garnets: theory and observations 121 (1992) 17
Cherepanova, T.A. and A.V. Stekolnikov, Computer simulation of molecular liquids on corrugated crystal surfaces 128 (1993) 116
Cherepanova, T.A., A.V. Stekolnikov and P. Bennema, Weighted-density functional approach for the solid–liquid interfaces in electrolytes 129 (1993) 202
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Chernov, A.A., E. Kaldis, M. Piechotka and M. Zha, Conductive and radiative heat transfer, diffusion and interface kinetics in spherically symmetric vapour growth; application to HgI_2 125 (1992) 627
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Chiareli, A.O.P. and M.G. Worster, On measurement and prediction of the solid fraction within mushy layers 125 (1992) 487
Chichibu, S., A. Iwai, S. Matsumoto and H. Higuchi, LP-MOCVD growth of $CuAlSe_2$ epitaxial layers 126 (1993) 635
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Chiu, T.H., M.D. Williams, T.K. Woodward, J.E. Cunningham, J.E. Zucker, T. Sizer, F.G. Storz, J.F. Ferguson and W.T. Tsang, The effect of growth temperature instability in the CBE growth of $In_xGa_{1-x}As_yP_{1-y}$/InP multiple quantum well structures 124 (1992) 165
Chiu, T.H., Y. Chen, J. Zucker, J.L. Marshall, S. Shunk and S.N.G. Chu, Selective area growth of InGaAsP/InP waveguide modulator structures by chemical beam epitaxy 127 (1993) 169
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Choyke, W.J., see Barrett 128 (1993) 358
Christoffersen, J. and M.R. Christoffersen, A revised theory for the growth of crystals by surface nucleation 121 (1992) 608
Christoffersen, J., see Christoffersen 121 (1992) 617
Christoffersen, M.R., see Christoffersen 121 (1992) 608
Christoffersen, M.R., and J. Christoffersen, Possible mechanisms for the growth of the biomaterial, calcium hydroxyapatite microcrystals 121 (1992) 617
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Chung, B.-C., K.R. Wickham, M. Ladle Ristow and J.G. Werthen, High efficiency GaAs-based multi-junction solar cells grown by metalorganic vapor phase epitaxy 124 (1992) 801
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Chung, C.K., see Yang 121 (1992) 717
Chung, C.K., J. Hwang, Y.H. Chang, W.J. Chen and L.P. Wang, The effect of temperature on the epitaxial quality of bilayers of iridium silicide and Si–Ge deposited on Si(100) in ultrahigh vacuum 126 (1993) 675
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Ciszek, T.F., T.H. Wang, R.W. Burrows and X. Wu, Growth of thin crystalline silicon layers for photovoltaic device use 128 (1993) 314
Claeys, C. and J. Vanhellemont, Recent progress in the understanding of crystallographic defects in silicon 126 (1993) 41
Clark, S.A., J.E. Macdonald, D.I. Westwood and R.H. Williams, Relaxation in $In_xGa_{1-x}As$/InP for compressive and tensile strain 121 (1992) 743
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Clawson, A.R., T.T. Vu, S.A. Pappert and C.M. Hanson, Effects of hydrogen-only interrupts on InGaAs/InP superlattices grown by OMVPE 124 (1992) 536
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Cockerill, T.M., J. Honig, D.V. Forbes, K.J. Beernink and J.J. Coleman, Characterization of electrical and optical loss of MOCVD regrowth in strained layer InGaAs–GaAs quantum well heterostructure lasers 124 (1992) 553
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Cotta, M.A. and M.M.G. de Carvalho, Monte Carlo simulation study on the flow conditions of a vacuum chemical epitaxy system 121 (1992) 429
Coudenys, G., I. Moerman, W. Vanderbauwhede, P. Van Daele and P. Demeester, Selective and shadow masked MOVPE growth of InP/InGaAs(P) heterostructures and quantum wells 124 (1992) 497
Coupat, B., J.P. Badaud, J.P. Fournier et Z. Bellemkhannate, Pression de vapeur de HgI_2 125 (1992) 644
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Craig, S.R., K.J. Roberts, J.N. Sherwood, K. Sato, Y. Hayashi, M. Iwahashi and R.J. Cernik, Using in-situ synthrotron radiation powder diffraction to characterize growth-related structural polymorphic phase transformations in cis-9-ω-octadecenoic acid 128 (1993) 1263
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Cros, B., see Meng 129 (1993) 610
Crosbie, M.J., see Mackey 129 (1993) 269
Crosio, M.-P. and M. Jullien, Fluorescence study of precrystallization of ribonuclease A: effect of salts 122 (1992) 66
Cross, E., see Burger 128 (1993) 1047
Crumbaker, T.E., J.Y. Natoli, I. Berbezier and J. Derrien, Growth of β-$FeSi_2$ on silicon substrates by chemical beam epitaxy 127 (1993) 158
Cui, Jie, Hailong Wang and Fuxi Gan, The optical and spectroscopic properties of II–VI wide-gap ZnSe/ZnS and ZnSe/ZnTe strained-layer superlattices (E) 121 (1992) 795
Cui, S.F., see Li 129 (1993) 532
Cuisinier, F.J.G., J.-C. Voegel, F. Apfelbaum and I. Mayer, High resolution electron microscopic study of a Ga-containing carbonate apatite 125 (1992) 1
Cullis, A.G., D.J. Robbins, A.J. Pidduck and P.W. Smith, The characteristics of strain-modulated surface undulations formed upon epitaxial $S_{1-x}Ge_x$ layers on Si 123 (1992) 333
Cullis, A.G., see Mackey 129 (1993) 269
Cunningham, J.E., see Chiu 124 (1992) 165
Cunningham, J.E., K.W. Goossen and W. Jan, Growth of pseudomorphic $In_xGa_{1-x}As/GaP_yAs_{1-y}$ multiple quantum well structures on GaAs by gas source molecular beam epitaxy 127 (1993) 184
Cunningham, J.E., V.J. Goldman, B. Su and W.Y. Jan, Peak-to-valley ratio of 130:1 at 1 K in AlGaAs/GaAs/AlGaAs tunneling structures: evidence for suppressed dopant segregation 127 (1993) 695
Cureton, C.G., see Thrush 124 (1992) 249
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Curreri, P.A., N. Ramachandran, J.P. Downey and J.C. Jones, Numerical modeling of melt velocity and thermal distributions during aircraft high-gravity arcs 130 (1993) 511

Da Silva, E.C.F., see Shibli 127 (1993) 700
Dabholkar, V. and R. Pollard, A model for the dynamics of island growth during deposition of compound semiconductors 121 (1992) 71
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Dabkowska, H., A. Dabkowski and J.E. Greedan, Flux growth of single crystals of $Nd_yPr_{1-y}GaO_3$ solid solutions as substrates for high temperature superconductor films 128 (1993) 699
Dabkowski, A., H. Dabkowska, J.E. Greedan, J.S. Xue and C.V. Stager, Growth and characterization of superconducting single crystals of layered 1212 PbSrYCaCu oxide 126 (1993) 471
Dabkowski, A., see Dabkowska 128 (1993) 699
Dabringhaus, H. and M. Haag, Interaction of molecular beams of KBr with (100) surfaces of KCl 127 (1993) 663
Dahmen, T., and R. Gruehn, Contributions on the thermal behaviour of sulfates. XI. On the chemical vapour transport of $Fe_2(SO_4)_3$ with HCl; thermochemical calculations and experimental results 130 (1993) 636
Dai, Ting-Arn, see Lin 123 (1992) 451
Dalas, E. and D. Fatouros, The effect of extremely low frequency (ELF) electric fields on biomineralization in vitro 125 (1992) 27
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Däweritz, L., RHEED studies of steps, islanding and faceting on singular, vicinal and high-index surfaces 127 (1993) 949
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Deng Mengxiang and Yang Xiuzhen, $Bi_6Te_2Mo_2O_{21}$ – a new synthetic crystal and its physical properties 128 (1993) 876
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Dhese, K.A., J.E. Nicholls, P.J. Wright, B. Cockayne and J.J. Davies, The growth of diffusion doped ZnSe:Te epilayers by atmospheric pressure metalorganic chemical vapour deposition 126 (1993) 179
Di Forte-Poisson, M.A., C. Brylinski, J. di Persio, X. Hugon, B. Vilotitch and C. Le Noble, $Ga_{1-x}In_xAs/InAs_yP_{1-y}/InP$ photodiodes for the 1.6 to 2.4 μm spectral region grown by low pressure MOCVD 124 (1992) 782
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Dondl, W., G. Lütjering, W. Wegscheider, J. Wilhelm, R. Schorer and G. Abstreiter, Sn and Sb segregation and their possible use as surfactant for short-period Si/Ge superlattices 127 (1993) 440
Dong, H.K., B.W. Liang, M.C. Ho, S. Hung and C.W. Tu, A study of Ar ion laser-assisted metalorganic molecular beam epitaxy of GaAs by reflection high-energy electron diffraction 124 (1992) 181
Dong Qiwei, see Wang 129 (1993) 774
Dong Rongkang, see Wang 129 (1993) 774
Donnelly, V.M., see McCrary 125 (1992) 320
Dormans, G.J.M., P.J. van Veldhoven and M. de Keijser, Composition-controlled growth of $PbTiO_3$ on $SrTiO_3$ by organometallic chemical vapour deposition 123 (1992) 537
Dörnen, A., see Moser 124 (1992) 333
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Dosanjh, S.S., P. Dawson, M.R. Fahy, B.A. Joyce, R.A. Stradling and R. Murray, Optical studies of the growth of single monolayer wide InAs quantum wells on GaAs by MBE 127 (1993) 579
Dotor, M.L., J. Meléndez, P. Huertas, A. Mazuelas, M. Garriga, D. Golmayo and F. Briones, Quantum well lasers with InAs monolayers in the active region grown at low temperature by atomic layer molecular beam epitaxy 127 (1993) 46
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Drevet, B., J.P. Garandet, D. Camel and J.J. Favier, Influence of thermal buoyancy on fibrous eutectic growth. I. Segregation results in the $Sn–Cu_6Sn_5$ system 129 (1993) 549
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Dryburgh, P.M., Further notes on the estimation of minimum temperature for crystal growth from a gas phase 130 (1993) 305

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Dunn, D.N., P. Xu and L.D. Marks, Problems with the use of surface reconstructions as indicators of a well-ordered surface 125 (1992) 543

Dunstan, D.J., R.H. Dixon, P. Kidd, L.K. Howard, V.A. Wilkinson, J.D. Lambkin, C. Jeynes, M.P. Halsall, D. Lancefield, M.T. Emeny, P.J. Goodhew, K.P. Homewood, B.J. Sealy and A.R. Adams, Growth and characterization of relaxed epilayers of InGaAs on GaAs 126 (1993) 589

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Dupouy, M.D., D. Camel and J.J. Favier, Natural convective effects in directional dendritic solidification of binary metallic alloys: dendritic array morphology 126 (1993) 480

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Elbaum, M., S.G. Lipson and J.G. Dash, Optical study of surface melting on ice 129 (1993) 491
Elgersma, A.V., M. Ataka and T. Katsura, Kinetic studies on the growth of three crystal forms of lysozyme based on the measurement of protein and Cl^- concentration changes 122 (1992) 31
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Elliott, A.G., A. Flat and D.A. Vanderwater, Silicon incorporation in LEC growth of single crystal gallium arsenide 121 (1992) 349
Elsaesser, D.W., J.E. Colon, Y.K. Yeo, R.L. Hengehold, K.R. Evans and J.S. Solomon, Erbium complexes and defect levels in MBE-grown erbium-doped GaAs and AlGaAs 127 (1993) 707
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Fahy, M.R., J.H. Neave, M.J. Ashwin, R. Murray, R.C. Newman, B.A. Joyce, Y. Kadoya and H. Sakaki, Incorporation of silicon during MBE growth of GaAs on (111)A substrates 127 (1993) 871
Faktor, D., M. Vesely and R. Harman, New method for III/V flux ratio calibration in MBE systems from arsenic pressure measurements 126 (1993) 499
Fan, G.H., R.D. Hoare, M.E. Pemble, I.M. Povey, A.G. Taylor and J.O. Williams, Gas phase monitoring of reactions under InP MOVPE growth conditions for the decomposition of tertiarybutyl phosphine and related precursors 124 (1992) 49
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Farrell, T., J.V. Armstrong, T.J. Bullough, R. Beanland, T.B. Joyce and P.J. Goodhew, Surface morphology of photo-assisted chemical beam epitaxial growth of gallium arsenide 127 (1993) 148
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Ferid, T., M. Ekawa, K. Yasuda, A. Tanaka and M. Saji, Variation of surface morphology with precursor supply ratio in MOVPE CdTe layers 128 (1993) 613
Fernández, J.M., J. Chen and H.H. Wieder, Transport parameters in pseudomorphic and strain-relaxed InGaAs heterojunctions grown by MBE on misoriented (100) GaAs substrates 127 (1993) 570
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Ferrand, B., D. Pelenc, I. Chartier and Ch. Wyon, Growth by LPE of Nd:YAG single crystal layers for waveguide laser applications 128 (1993) 966
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Frigo, D.M., W.W. van Berkel, W.A.H. Maassen, G.P.M. van Mier, J.H. Wilkie and A.W. Gal, A method for dosing solid sources for MOVPE: excellent reproducibility of dosimetry from a saturated solution of trimethylindium 124 (1992) 99
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Fujita, K., S. Fukatsu, Y. Shiraki, H. Yaguchi and R. Ito, Intersubband absorption in n-type $Si/Si_{1-x}Ge_x$ multiple quantum well structures formed by Sb segregant-assisted growth 127 (1993) 416
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Gérard, J.-M., High resolution in situ measurement of the surface composition of $In_xGa_{1-x}As$ and $In_xAl_{1-x}As$ at growth temperature 127 (1993) 981
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Gerson, A.R., K.J. Roberts, J.N. Sherwood, A.M. Taggart and G. Jackson, The role of growth environment on the crystallization of normal alkanes in the homologous series from $C_{18}H_{38}$ to $C_{29}H_{60}$ 128 (1993) 1176
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Graham, R.M., N.J. Mason, P.J. Walker, D.M. Frigo and R.W. Gedridge, Jr., MOVPE growth of InSb on GaAs substrates 124 (1992) 363
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Grasza, K., U. Zuzga-Grasza, A. Jędrzejczak, R.R. Gałązka, J. Majewski, A. Szadkowski and E. Grodzicka, A novel method of crystal growth by physical vapour transport and its application to CdTe 123 (1992) 519
Grasza, K. and A. Jędrzejczak, Melt dynamics in directional solidification of PbSnTe 128 (1993) 183
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Guilloteau, J.-P., M.M. Riès-Kaut and A.F. Ducruix, Variation of lysozyme solubility as a function of temperature in the presence of organic and inorganic salts 122 (1992) 223
Guimarães, F.E.G., B. Elsner, R. Westphalen, B. Spangenberg, H.J. Geelen, P. Balk and K. Heime, LP-MOVPE growth and optical characterization of GaInP/GaAs heterostructures: interfaces, quantum wells and quantum wires 124 (1992) 199
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Hageman, P.R., A. van Geelen, W. Gabriëlse, G.J. Bauhuis and L.J. Giling, Optical and electrical quality of InGaP grown on GaAs with low pressure metalorganic chemical vapour deposition 125 (1992) 336
Hageman, P.R., M.H.J.M. de Croon, X. Tang and L.J. Giling, Pressure and temperature dependence of Zn incorporation in metalorganic chemical vapour deposition grown GaAs and AlGaAs using diethylzinc as precursor 129 (1993) 281
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Hamza, S.H. and S.K. Hamdona, The kinetics of dissolution of calcium fluoride in the presence of some metal ions 125 (1992) 591
Han, J.C., see Beda 121 (1992) 394
Han, Jianru, Yusheng Liu, Min Wang and Dezhen Nie, Flux growth and properties of $RbTiOAsO_4$ (RTA) crystals 128 (1993) 864
Han, P.D., L. Chang and D.A. Payne, Top-seeded growth of superconducting $(Ba_{1-x}K_x)BiO_3$ crystals by an electrochemical method 128 (1993) 798
Hanafusa, H., E. Taguchi, H. Ogata and K. Yoneda, $Si_{1-x}Ge_x$/sapphire structure fabricated by molecular beam epitaxy 127 (1993) 430
Hanna, M.C., Z.H. Lu, E.G. Oh, E. Mao and A. Majerfeld, Intrinsic carbon incorporation in very high purity MOVPE GaAs 124 (1992) 443
Hannick, L.I., M.A. Perozzo, L.W. Schultz and K.B. Ward, A PC-based spreadsheet for tracking results of crystallization experiments 122 (1992) 303
Hansen, K., E. Peiner, A. Schlachetzki, W. Möhling and H. Menniger, Zn-doped In GaAsP (1.3 μm) contact layer for an inverted DH laser structure 125 (1992) 465
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Hansson, P.O., A. Gustafsson, M. Albrecht, R. Bergmann, H.P. Strunk and E. Bauser, High quality Ge_xSi_{1-x} by heteroepitaxial lateral overgrowth 121 (1992) 790
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Harding, M.M., R.J. Rule, R.J. Oldman and R.J. Davey, Growth rate dispersion in small crystals and its relation to mosaic spread 123 (1992) 373
Hardtdegen, H., M. Hollfelder, R. Meyer, R. Carius, H. Münder, S. Frohnhoff, D. Szynka and H. Lüth, MOVPE growth of GaAs using a N_2 carrier 124 (1992) 420
Hardtdegen, H., see Meyer 124 (1992) 583
Härle, V., B. Rose, D. Robein, Y. Gao, E. Landsbeck and F. Scholz, Chlorine assisted selective area epitaxy in AP-MOVPE of InP: influence of CCl_4 on growth and on Zn and Si incorporation 124 (1992) 260
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Hayakawa, Y., K. Asakawa, Y. Torimoto, K. Yamashita, A. Nakayama and M. Kumagawa, Influence of the solute convection on InGaSb LPE layers on vertically mounted GaSb substrates 128 (1993) 159
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Jiang, M., J.G. Huang, Y.Z. Wang, C. Zhang, D.C. Zeng, X. Wang and G.W. Qiao, Solidification characteristics of textured 123 phase in YBCO by laser floating zone leveling (LFZL) method 130 (1993) 389
Jiang, M.H., Guan 125 (1992) 568
Jiang, Min-hua, see Zhang 123 (1992) 255
Jiang, Q.Z., see Chen 128 (1993) 880
Jiang, X.S., A.R. Clawson and P.K.L. Yu, Study of interrupted MOVPE growth of InGaAs/InP superlattice 124 (1992) 547
Jin, D.J., see Li 128 (1993) 1092
Jin, Weiqing and K. Tsukamoto, Anisotropic growth of $LiNbO_3$ crystal as revealed by high temperature in situ observation 123 (1992) 327
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Jobst, B., see Heinecke 124 (1992) 170
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Johansen, T.H., Diverging growth velocity predicted by the dynamic equations of the Czochralski process 126 (1993) 347
Johnson, F.G., B.L. Olmsted, S. Chen and G.W. Wicks, Tilted superlattice composition profile measured by photoluminescence and Raman 127 (1993) 812
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Johnson, M.B., U. Maier, H.-P. Meier and H. Salemink, Atomic-scale view of AlGaAs/GaAs multilayers with cross-sectional scanning tunneling microscopy 127 (1993) 1077
Jones, A.C., see Gerrard 121 (1992) 500
Jones, A.C., P.A. Lane, T. Martin, R.W. Freer, P.D.J. Calcott, M.R. Houlton and C.R. Whitehouse, New metalorganic gallium precursors for the growth of GaAs and AlGaAs by CBE 124 (1992) 81
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Jones, A.C., Metalorganic precursors for vapour phase epitaxy 129 (1993) 728
Jones, A.C., S.A. Rushworth, P. O'Brien, J.R. Walsh and C. Meaton, The use of dimethylzinc-amine adducts for the p-doping of InP and related alloys 130 (1993) 295
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Jones, E.D., N.M. Stewart and J.B. Mullin, Studies on the self-diffusion of cadmium in cadmium telluride in the temperature range 350–650°C using anodic oxidation 130 (1993) 6
Jones, E.Y., D.I. Stuart, E.F. Garman, R. Griest, D.C. Phillips, G.L. Taylor, O. Matsumoto, G. Darby, B. Larder, D. Lowe, K. Powell, D. Purifoy, C.K. Ross, D. Somers, M. Tisdale and D.K. Stammers, The growth and characterization of crystals of human immunodeficiency virus (HIV) reverse transcriptase 126 (1993) 261
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Jordan, A.S., E.M. Monberg and J.E. Clemans, Thermal stress theory of dislocation reduction in the vertical gradient freeze (VGF) growth of GaAs and InP 128 (1993) 444
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Kadoya, Y., see Fahy 127 (1993) 871
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Kanai, H., S. Motoyama, M. Kimura, A. Tanaka and T. Sukegawa, Gravity effect on liquid phase epitaxy of Si 128 (1993) 310
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Karasawa, S., M. Mitsuhashi, S. Ohya, K. Kobayashi, T. Watanabe, K. Hirai, K. Horiguchi and F. Togashi, Crystal growth of epitaxial CVD diamond using ^{13}C isotope and characterization of dislocations by Raman spectroscopy 128 (1993) 403
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Katsumata, T., H. Konoura, A. Konno, K. Takei, M. Shinohara and K. Takahashi; Moisture contents of $Li_2B_4O_7$ glass and single crystals 121 (1992) 737
Katsumata, T., H. Ishijima, T. Sugano, M. Yamagishi and K. Takahashi, Preparation of starting materials of β-BaB_2O_4 by zone melting 123 (1992) 597
Katsumata, T., K. Ohshima, K. Oe, M. Hisamoto, T. Ohtaki, H. Konoura, H. Nakagawa and K. Takahashi, Non-wetting container material for growing lithium and barium borate crystals 125 (1992) 270
Katsumata, T., H. Konoura, H. Imagawa, A. Konno, K. Takei, M. Shinohara, K. Kano and K. Takahashi, Growth and characterization of $Li_2B_4O_7$ single crystals grown by novel Bridgman technique using a graphite container 128 (1993) 924
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Katsuyama, T., I. Yoshida, J. Hashimoto, Y. Taniguchi and H. Hayashi, OMVPE growth of AlGaInP/$Ga_xIn_{1-x}P$ strained quantum well structures and their applications to visible laser diodes 124 (1992) 697
Kaul, P., A. Schütze, D. Kohl, A. Brauers and M. Weyers, Surface chemistry of new As precursors for MOVPE and MOMBE: phenylarsine and tertiarybutylarsine on GaAs(100) 123 (1992) 411
Kaviani, K., K. Hu, Q. Xie and A. Madhukar, Realization of high performance doped-channel MISFETs in highly strained AlGaAs/InGaAs/AlGaAs based quantum wells 127 (1993) 68
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Kawahara, N., see Hoshizaki 121 (1992) 53
Kawai, T., H. Yonezu, Y. Yamauchi, M. Lopez, K. Pak and W. Kürner, Initial growth process of GaAs on Ge substrate and pseudomorphic Si interlayer 127 (1993) 107
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Kawamoto, M., see Yoshikawa 122 (1992) 298
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Kim, S.D. and J.S. Harris, Jr., Stacking fault stability in GaAs/Si hetero-epitaxial growth 123 (1992) 439
Kim, S.D., see Lord 127 (1993) 759
Kim, S.I., K.S. Eom, Y. Kim, M.S. Kim, S.K. Min, C. Lee, M.H. Kwak and D.S. Ma, Characteristics of heavily carbon-doped GaAs by LPMOCVD and critical layer thickness 126 (1993) 441
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Kimura, H., I. Petrov, F. Adibi and J.E. Greene, Growth and microstructure of epitaxial 45°-rotated bcc W layers on NaCl-structure MgO(001) substrates and TiN(001) buffer layers 123 (1992) 344
Kimura, K., see Inoue 127 (1993) 1041
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Kirchner, P.D., see Melloch 127 (1993) 499
Kirchner, P.D., A. Vaterlaus, R.M. Feenstra, C. Lin, G.D. Pettit and J.M. Woodall, Solubility-limit activation of Si doping at MBE GaAs pn junctions observed by cross-sectional scanning tunneling microscopy 127 (1993) 1030
Kirk, J.B., see York 124 (1992) 709
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Kitano, M., T. Hamabe, S. Maeda and T. Okabe, Morphology and growth mechanism of new-shaped ZnO crystals 128 (1993) 1099
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Kobayashi, N. and Y. Yamauchi, Enhancement of AsH_3 decomposition on highly doped p-GaAs surfaces 124 (1992) 44
Kobayashi, N. and Y. Kobayashi, In situ control of heterointerface quality in MOVPE by surface photo-absorption 124 (1992) 525
Kobayashi, R., T. Okahisa, M. Shiozaki and F. Hasegawa, Effects of NH_3 on the growth rate and the surface morphology of GaAs in chloride VPE 125 (1992) 457
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Kohzen, A., Y. Tohmori, Y. Akatsu and H. Kamada, MOVPE growth of InGaAs/InAlAs using trimethylamine alane for photonic and electronic devices 124 (1992) 70
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Kondo, M., C. Anayama, T. Tanahashi and S. Yamazaki, Crystal orientation dependence of impurity dopant incorporation in MOVPE-grown III–V materials 124 (1992) 449
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Korte, L., Chr. Thanner, M. Huber and Ch. Hoyler, Selective area growth of GaAs and AlGaAs with TMGa, TMAl, AsH_3 and HCl by atmospheric pressure MOVPE 124 (1992) 220
Korytár, D., V. Daniška, I. Priecel and M. Babinský, Large-area X-ray and CL study of SI GaAs wafers from various suppliers 121 (1992) 440
Korytár, D., Point-like and extended defects in Si and GaAs 126 (1993) 30
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Koùkitu, A., T. Miyazawa, H. Ikeda and H. Seki, Atmospheric pressure atomic layer epitaxy of ZnS using Zn and H_2S 123 (1992) 95
Koukitu, A., see Ikeda 123 (1992) 213
Kouta, H., S. Imoto and Y. Kuwano, β-BaB_2O_4 single crystal growth by Czochralski method using α-BaB_2O_4 and β-BaB_2O_4 single crystals as starting material 128 (1993) 938
Kovác, J., A. Šatka and B. Rheinländer, Electro-optic properties of InGaAs/InP multi-quantum well PIN structures 126 (1993) 151
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Krasnov, A.N., Yu.N. Purtov, Yu.F. Vaksman and V.V. Serdyuk, ZnSe blue-light-emitting diode 125 (1992) 373
Kraus, J., H. Meschede, Q. Liu, W. Prost, F.J. Tegude, H. Lakner and E. Kubalek, $In_yGa_{1-y}As$/GaAs interface smoothing by GaAs monolayers in highly strained graded superlattice channels ($0.2 \leq y \leq 0.4$) for pseudomorphic $Al_xGa_{1-x}As$/$In_yGa_{1-y}As$ HFET 127 (1993) 589
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Kudoh, M., X. Hu, K. Ohno and Y. Kawazoe, New cluster–cluster aggregation model for formation process of fractal structure in sol–gel transition of SiO_2 128 (1993) 1162
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Kühne, H., On a substituting sticking and trapping model of CVD $Si_{1-x}Ge_x$ layer growth 125 (1992) 291
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Lazzari, J.L., C. Fouillant, P. Grunberg, J.L. Leclercq, A. Joullié and C. Schiller, Critical layer thickness in AlGaAsSb/GaSb heterostructures determined by X-ray diffraction 130 (1993) 96
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Lee, J.-K., J.-K. Park and K.Y. Eun, Effects of gravity and temperature gradient on the diamond formation during synthesis at 4.4 GPa and 1300°C 125 (1992) 51
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Lee, M.K., R.H. Horng and L.C. Haung, Metalorganic chemical vapor deposition growth of $Ga_{0.5}In_{0.5}P$ ordered alloys by phosphine modulation 124 (1992) 358
Lee, S.H., Y.J. Kim, S.H. Cho and E.P. Yoon, The influence of the Czochralski growth parameters on the growth of lithium niobate single crystals 125 (1992) 175
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Li, J.H., Z.H. Mai, S.F. Cui, Z.H. Chen and M.H. Li, Characterization of $Al_xGa_{1-x}As/Al_yGa_{1-y}As/GaAs$ step multi-quantum wells on (001) GaAs by X-ray double-crystal diffraction 129 (1993) 532
Li, L. and N. Rodríguez-Hornedo, Growth kinetics and mechanism of glycine crystals 121 (1992) 33
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Li Zhengdong, Su Genbo and Wu Baichang, Growth and characterization of methyl p-hydroxybenzoate (p-MHB) 121 (1992) 516
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Libatique, N., A. Sasaki, D. Choi, S. Wada, A.C. Rastogi, M. Kimata, K. Kaneko and M. Takashima, CdTe/InSb/α-Sn heterostructures grown by molecular beam epitaxy 127 (1993) 296
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Lin, J.F., M.J. Jou, C.Y. Chen and B.J. Lee, Effect of substrate misorientation on the optical properties and hole concentration of $Ga_{0.5}In_{0.5}P$ and $(Al_{0.5}Ga_{0.5})_{0.5}In_{0.5}P$ grown by low pressure metalorganic vapor phase epitaxy 124 (1992) 415
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Lin, Wei, Yuan-Kuang Tu, Ting-Arn Dai, Wen-Jeng Ho, Gwo-Yue Lee and Hung-Pin Shiao, The $In_xGa_{1-x}As_yP_{1-y}$ ($0.53 < x < 1$, $0 < y < 1$) compound semiconductor for LD structures by organometallic vapor-phase epitaxy 123 (1992) 451
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Lorber, B. and R. Giegé, A versatile reactor for temperature controlled crystallization of biological macromolecules 122 (1992) 168
Lorber, B., M. Skouri, J.-P. Munch and R. Giegé, The influence of impurities on protein crystallization; the case of lysozyme 128 (1993) 1203
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Mace, D.R., M.P. Grimshaw, D.A. Ritchie, A.G. Churchill, M. Pepper and G.A.C. Jones, the growth and physical properties

of high quality pseudomorphic In_x-$Ga_{1-x}As$ HEMT structures 127 (1993) 601
Macfarlane, R.M., see Chaminade 128 (1993) 1031
Machida, H., K. Hoshikawa and T. Fukuda, Growth of TiO_2 ribbon single crystals by edge-defined film-fed growth method 128 (1993) 829
Mackey, K.J., see Vere 121 (1992) 62
Mackey, K.J., G.M. Williams, M.J. Crosbie, A.G. Cullis and B. Cockayne, A study of titanium-doped yttrium orthoaluminate using scanning photoluminescence and low temperature cathodoluminescence 129 (1993) 269
Madar, R., see Ghez 123 (1992) 317
Madella, M., A. Bosacchi, S. Franchi, P. Allegri and V. Avanzini, Study of ALMBE growth conditions for the preparation of compositionally graded AlGaAs/GaAs structures 127 (1993) 270
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Madhukar, A., see Rajkumar 127 (1993) 863
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Maeda, H., S. Masuda, K. Kusakabe and S. Morooka, Nucleation and growth of diamond in a microwave plasma on substrate pretreated with non-oxide ceramic particles 121 (1992) 507
Maeda, K., Y. Yamashita, K. Fujita, S. Fukatsu, K. Suzuki, Y. Mera and Y. Shiraki, On optimum design of dislocation filters for reduction of misfit dislocations 127 (1993) 451
Maeda, S., see Kitano 128 (1993) 1099
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Maehashi, K., S. Hasegawa and H. Nakashima, Effects of SiAsBeAs interface structure on the initial stages of GaAs MBE growth on Si(111) 127 (1993) 98
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Malinina, L., see Minasov 122 (1992) 136
Malkin, A.J., J. Cheung and A. McPherson, Crystallization of satellite tobacco mosaic virus. I. Nucleation phenomena 126 (1993) 544
Malkin, A.J. and A. McPherson, Crystallization of satellite tobacco mosaic virus. II. Postnucleation events 126 (1993) 555
Malkin, A.J. and A. McPherson, Light scattering investigations of protein and virus crystal growth: ferritin, apoferritin and satellite tobacco mosaic virus 128 (1993) 1232
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Manne, S., J.P. Cleveland, G.D. Stucky and P.K. Hansma, Lattice resolution and solution kinetics on surfaces of amino acid crystals: an atomic force microscope study 130 (1993) 333
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Mazuelas, A., J. Meléndez, P.S. Domínguez, M. Garriga, C. Ballesteros, D. Gerthsen and F. Briones, Structural and optical characterization of alternately strained GaAs/GaP/GaAs/InP superlattices grown by atomic layer 127 (1993) 623
Mazzer, M., F. Romanato, A.V. Drigo and A. Carnera, Mechanisms of strain relaxation in III–V semiconductor heterostructures 126 (1993) 125
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surements in a horizontal, low-pressure metalorganic chemical vapor deposition reactor by infrared laser interferometric thermometry 125 (1992) 320
McDaniel, A.H., B. Liu and R.F. Hicks, Coupled gas and surface reactions in the organometallic vapor-phase epitaxy of cadmium telluride 124 (1992) 676
McElroy, H.E., G.W. Sisson, W.E. Schoettlin, R.M. Aust and J.E. Villafranca, Studies on engineering crystallizability by mutation of surface residues of human thymidylate synthase 122 (1992) 265
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Meier, H.P., R.F. Broom, P.W. Epperlein, S. Hausser, A. Jakubowicz and W. Walter, Growth investigations of 1.3 μm GaInAsP/InP MQW laser diodes grown by chemical beam epitaxy 127 (1993) 165
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Meng, Qingju, Baijun Chen, Guohua Hou, Lianmin Wu and Guang Dong, Modified hot wall epitaxy (HWE) apparatus and preparation of ZnS_xSe_{1-x} films 121 (1992) 191
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Meyer, B.K., C. Wetzel, M. Drechsler, A. Moll, H. Linke, P. Omling and F. Scholz, Novel applications of contactless characterization techniques in epitaxial crystals and quantum well structures 128 (1993) 567
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Million, A., T. Colin, P. Ferret, J.P. Zanatta, P. Bouchut, G.L. Destéfanis and J.

Bablet, HgCdTe double heterostructure for infrared injection laser 127 (1993) 291
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Minagawa, S., Y. Ishitani and T. Tanaka, Epitaxial growth of AlGaInP lattice-matched to GaAsP substrates by organo-metallic vapor phase epitaxy 126 (1993) 539
Minasov, G., V. Tereshko, B. Chernov and L. Malinina, An efficient and possibly general packing mode for crystals of B-DNA oligonucleotides 122 (1992) 136
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Mirin, R., M. Krishnamurthy, I.-H. Tan, J.E. Bowers, A.C. Gossard and E.L. Hu, Morphology and optical properties of strained InGaAs quantum wires 127 (1993) 881
Mirin, R., M. Krishnamurthy, J. Ibbetson, J. English and A. Gossard, Observation of quasi-periodic facet formation during high temperature growth of AlAs and AlAs/GaAs superlattices 127 (1993) 908
Mishima, T., T. Tanimoto, M. Kudoh and M. Takahama, High mobility and high sheet electron density in selectively doped InAlAs/InGaAs heterostructures grown by MBE on GaAs 127 (1993) 770
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Miyake, H. and K. Sugiyama, THM growth and properties of $CuInSe_2$ single crystals 125 (1992) 548
Miyake, H., M. Hata and K. Sugiyama, Solution growth of $CuGaS_2$ and $CuGaSe_2$ using CuI solvent 130 (1993) 383
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Miyazaki, N., H. Uchida, T. Munakata, K. Fujioka and Y. Sugino, Thermal stress analysis of silicon bulk single crystal during Czochralski growth 125 (1992) 102
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Miyazawa, S., M. Sasaura and M. Mukaida, Single crystal growth of rare-earth gallates and epitactic growth nature of high-T_c superconducting YBCO thin films on them 128 (1993) 704
Miyazawa, T., see Koukitu 123 (1992) 95
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Miyoshi, S., K. Onabe, N. Ohkouchi, H. Yaguchi, R. Ito, S. Fukatsu and Y. Shiraki, MOVPE growth of cubic GaN on GaAs using dimethylhydrazine 124 (1992) 439
Mizuguchi, K., see Kadoiwa 124 (1992) 757
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Mo, P.G., H.Z. Tan, L.X. Du and X.Q. Fan, A novel technique for Czochralski growth of GaSb single crystals 126 (1993) 613
Möck, P., Complete characterization of epitaxial systems from the lattice geometrical point of view. I. Fundamentals 128 (1993) 122
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Mokler, S.M., N. Ohtani, M.H. Xie, X. Zhang and B.A. Joyce, Growth rate dependence on GeH_4 during gas source MBE of Si_xGe_{1-x} alloys grown from Si_2H_6 and GeH_4 127 (1993) 467
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Moser, M., C. Geng, E. Lach, I. Queisser, F. Scholz, H. Schweizer and A. Dörnen, Optical characterization of MOVPE grown GaInP layers 124 (1992) 333
Mosley, W.D., J.Z. Liu, A. Matsushita, Y.P. Lee, P. Klavins and R.N. Shelton, Preparation and superconductivity of $Ba_{1-x}K_xBiO_3$ single crystals 128 (1993) 804
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Munns, G.O., M.E. Sherwin, Y. Kwon, T. Brock, W.L. Chen, D. Pavlidis and G.I. Haddad, Parametric investigation of InGaAs/InAlAs HEMTs grown by CBE 127 (1993) 25
Munns, G.O., W.L. Chen, M.E. Sherwin and G.I. Haddad, The growth of InAlP using trimethyl amine alane by chemical beam epitaxy 127 (1993) 226
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Nagle, J., J.P. Landesman, M. Larive, C. Mottet and P. Bois, Indium surface segregation in strained GaInAs quantum wells grown on GaAs by MBE 127 (1993) 550
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Ostrogorsky, A.G., H.J. Sell, S. Scharl and G. Müller, Convection and segregation during growth of Ge and InSb crystals by the submerged heater method 128 (1993) 201
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Pan Peicong, Zhu Hongbin, Yan Shenhui, Chai Yiao, Wang Siting and Hou Yinchun, Distribution and valence of chromium in forsterite crystals grown by the Czochralski technique 121 (1992) 141
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Pascal-Delannoy, F., N.J. Mason, G. Bougnot, P.J. Walker, J. Bougnot, A. Giani and G.G. Allogho, InGaSb/GaSb photodiodes grown by MOVPE 124 (1992) 409
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Philippot, E., A. Ibanez, A. Goiffon, M. Cochez, A. Zarka, B. Capelle, J. Schwartzel and J. Détaint, A quartz-like material: gallium phosphate ($GaPO_4$); crystal growth and characterization 130 (1993) 195
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Ruiz, X., V. Nikolov, F. Sandiumenge, R. Solé, R. Cabré, M. Aguiló and F. Díaz, Solvents for the growth of $BaFe_{12-(x+y)}Co_xSn_yO_{10}$ bulk crystals from high-temperature solution 128 (1993) 1273
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Sakaguchi, H., T. Tsuchiya, T. Meguro, H. Nagai and S. Kuma, MOVPE growth of Si planar-doped AlGaAs/InGaAs pseudomorphic HEMT structures 124 (1992) 519
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Samuelson, L., B. Junno, G. Paulsson, J.O. Fornell and L. Ledebo, CBE growth of (001) GaAs: RHEED and RD studies 124 (1992) 23
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Sant, C., P. Gibart, P. Genou and C. Vèrié, Metalorganic chemical vapor deposition of $YBa_2Cu_3O_{7-x}$ using a special equipment for solid precursors 124 (1992) 690
Santiso, J., A. Figueras, R. Rodrígeuz-Clemente, B. Armas, C. Combescure, A. Mazel, Y. Kihn and J. Sévely, MOCVD SiC layer morphology and texture dependence on thickness and total pressure 128 (1993) 363
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Schindler, W., P. van Hasselt, P. Tontsch, J. Markl, J. Burger, P. Bauer and G. Saemann-Ischenko, Molecular beam epitaxy of precipitation free high temperature $SmBa_2Cu_3O_{7-\delta}$ superconductor thin films with small surface roughness 127 (1993) 1088
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Schmidbauer, W., T. Wilke and W. Assmus, In-situ observation of growth morphologies in systems with high melting temperatures 128 (1993) 240
Schmidt, H.P., W. Koerver and B. Pätz, Practical aspects of crystal growth experiments on board EURECA-1 122 (1992) 317
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Schneider, Jr., R.P., R.P. Bryan, E.D. Jones, R.M. Biefeld and G.R. Olbright, Trimethylamine alane for MOVPE of AlGaAs and vertical-cavity surface-emitting laser structures 123 (1992) 487
Schneider, Jr., R.P., R.P. Bryan, J.A. Lott, E.D. Jones and G.R. Olbright, MOVPE growth of InAlGaP-based visible vertical-cavity surface-emitting lasers 124 (1992) 763
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Sears, B., R. Narayanan, T.J. Anderson and A.L. Fripp, Convection of tin in a Bridgman system. I. Flow characterization by effective diffusivity measurements 125 (1992) 404
Sears, B., A.L. Fripp, W.J. Debnam, Jr., G.A. Woodell, T.J. Anderson and R. Narayanan, Convection of tin in a Bridgman system. II. An electrochemical method for detecting flow regimes 125 (1992) 415
Seidel-Salinas, L.K., S.H. Jones and J.M. Duva, A semi-empirical model for the complete orientation dependence of the growth rate for vapor phase epitaxy: chloride VPE of GaAs 123 (1992) 575
Seifert, W., K. Deppert, J.O. Fornell, X. Liu, S. Nilsson, M.-E. Pistol and L. Samuelson, Analysis of growth conditions for the deposition of monolayers of GaInAs, GaAs and InAs in InP by LP-MOVPE 124 (1992) 531
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Shan, L., L.W. Guddat, R.L. Raison and A.B. Edmundson, Crystallization of an Fv fragment from a human IgM cryoglobulin by a microseeding technique 126 (1993) 229
Shang, S.X., H. Wang and X.L. Sheng, Growth mechanism and crystal habit of $RBa_2Cu_3O_{7-x}$ (R = Y, Tm, Gd) single crystals 129 (1993) 411
Shao, Zong-shu, see Zhang 123 (1992) 255
Sharp, J.W. and D. Eres, In situ observation of surface-limited Ge growth processes by transient optical reflectometry 125 (1992) 553
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Shea, J.S., B.T. You, J.Y. Kao, J.R. Deng, Y.S. Chang and T.P. Chen, Large area epitaxial method for high brightness 655 nm AlGaAs double heterostructure red LEDs 128 (1993) 533
Shelton, R.N., see Zhang 128 (1993) 734
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Shen, A., L. Xu, H. Wang, Y. Chen, Z. Wang and A.Z. Li, Undoped and Sb-doped ZnSe-based II–VI superlattices grown by molecular beam epitaxy 127 (1993) 383
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Sherwood, J.N., see Bhat 121 (1992) 709
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Sherwood, J.N. and G.S. Simpson, The growth, structural and optical characterization of large area, single crystalline thin films of 3-nitroaniline (mNA) 128 (1993) 981
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Shibli, S.M., A.B. Henriques, C.A.C. Mendonça, E.C.F. da Silva, E.A. Meneses, L.M.R. Scolfaro and J.R. Leite, Electronic properties of multiple Si δ-doped GaAs layers grown by molecular beam epitaxy and migration-enhanced epitaxy 127 (1993) 700
Shibukawa, A., see Katoh 130 (1993) 123
Shieh, H.M., T.S. Wu and W.C. Hsu, SiH_4-doped AlGaAs epilayers formed by MOCVD 121 (1992) 665
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Shimamura, K., M. Timoshechkin, T. Sasaki, K. Hoshikawa and T. Fukuda, Growth and characterization of calcium niobium gallium garnet (CNGG) single crystals for laser applications 128 (1993) 1021
Shimizu, M., see Inoue 123 (1992) 615
Shimizu, T., H. Nonaka and K. Arai, Thin film growth behavior of $YBa_2Cu_3O_{7-\delta}$ in sequential deposition with high-purity ozone gas 128 (1993) 793
Shimoyama, K., Y. Inoue, K. Fujii and H. Gotoh, Novel selective area growth of AlGaAs and AlAs with HCl gas by MOVPE 124 (1992) 235
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Shirtcliffe, T.G.L. and R.C. Kerr, On the use of electrical resistance and temperature as measures of the solid fraction in a mushy layer 125 (1992) 495

Shitara, T., J. Zhang, J.H. Neave and B.A. Joyce, As/Ga ratio dependence of Ga adatom incorporation kinetics at steps on vicinal GaAs(001) surfaces 127 (1993) 494
Shripathi, T., see Bhat 121 (1992) 709
Shukri, Z.A., C.H. Champness and I. Shih, Boron nitride powder coating of ampoule for Bridgman-grown $CuInSe_2$ 129 (1993) 107
Shumov, D.P., M.P. Tarassov and V.S. Nikolov, Investigation of optical inhomogeneities in $KTiOPO_4$ (KTP) single crystals grown from high-temperature tungsten-containing solutions 129 (1993) 635
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Simpson, J., S.Y. Wang, I. Hauksson, H. Stewart, S.J.A. Adams, K.A. Prior and B.C. Cavenett, Effects of UV laser irradiation on the growth of nitrogen-doped p-type ZnSe 127 (1993) 327
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Singh, N.B., M. Gottlieb, T. Henningsen, R.H. Hopkins, R. Mazelsky, M.E. Glicksman, S.R. Coriell, W.M.B. Duval and G.J. Santoro, Effect of growth conditions on the quality of lead bromide crystals 123 (1992) 227
Singh, N.B., T. Henningsen, R.H. Hopkins, R. Mazelsky, R.D. Hamacher, E.P. Supertzi, F.K. Hopkins, D.E. Zelmon and O.P. Singh, Nonlinear optical characteristics of binary organic system 128 (1993) 976
Singh, N.B., M. Gottlieb, R. Mazelsky and W.M.B. Duval, The optical quality of mercurous halide crystals 128 (1993) 1053
Singh, O.P., see Singh 128 (1993) 976
Singh, Y., D.P. Goswami, M. Bala and M.L. Kalra, Large needle-shaped highly conducting organic charge transfer complexes with asymmetric donor molecules 123 (1992) 601
Sinha, A.K., D.M. Wayne and R. Essex, Flux growth of pure and doped zircons 125 (1992) 431
Siredey, N., M. Boufoussi, S. Denis and J. Lacaze, Dendritic growth and crystalline quality of nickel-base single grains 130 (1993) 132
Sirringhaus, H., see Onda 127 (1993) 634
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Skouri, M., J.-P. Munch, B. Lorber, R. Giegé and S. Candau, Interactions between lysozyme molecules under precrystallization conditions studied by light scattering 122 (1992) 14
Skouri, M., see Lorber 128 (1993) 1203
Škrtić, D., N. Filipović-Vinceković and V. Babić-Invančić, The effect of dodecylammonium chloride on crystal growth of calcium oxalate 121 (1992) 197
Škrtić, D. and H. Füredi-Milhofer, Influence of some aminoacids on the spontaneous precipitation of calcium oxalate from high ionic strength solutions 129 (1993) 449
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Smith, G.W., A.J. Pidduck, C.R. Whitehouse, J.L. Glasper and J. Spowart, Real-time laser-light scattering studies of surface topography development during GaAs MBE growth 127 (1993) 966
Smith, J.S., see Wu 127 (1993) 896
Smith, L.M., see Gerrard 121 (1992) 500
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Snyder, D.W., P.J. Sides and E.I. Ko, On the rate and uniformity of CdTe deposition in an impinging jet reactor: numerical simulations 121 (1992) 631
Snyder, D.W., P.J. Sides and E.I. Ko, On the rate and uniformity of CdTe deposition in an impinging jet reactor: experimental results 123 (1992) 163
Sobiesierski, Z., see Woolf 127 (1993) 913
Söhnel, O., A. Costa-Bauzá and V. Velich, Calcium oxalate monohydrate precipitation investigation by thermometric method 126 (1993) 493
Sokołowska, A. and A. Olszyna, Photon assisted chemical synthesis of E-BN 121 (1992) 733
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Sorba, L., G. Biasiol, G. Bratina, R. Nicolini and A. Franciosi, Charged versus neutral interfaces in III–V/Ge quantum wells 127 (1993) 93
Sorba, L., G. Bratina, A. Franciosi, L. Tapfer, G. Scarmarcio, V. Spagnolo, A. Migliori, P. Merli and E. Molinari, Si–GaAs(001) superlattice structure 127 (1993) 121
Sorba, L., see Bratina 127 (1993) 387
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Soulière, V., P. Abraham, J. Bouix, M.P. Berthet, Y. Monteil, A.M. Pougnet, R. Mellet, A. Ougazzaden and A. Mircea, Use of high purity trimethylindium–trimethylamine adduct in MOVPE in InP 124 (1992) 93
Sousa, R., Y.J. Chung, B.-C. Wang and E.M. Lafer, Single crystals of chimeric T7/T3 RNA polymerase with T3 promoter specificity 122 (1992) 366
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Többen, D., F. Schäffler, M. Besson, C.M. Engelhardt, A. Zrenner, G. Abstreiter and E. Gornik, High mobility two-dimensional electron gases in $Si/Si_{1-x}Ge_x$ heterostructures grown by MBE 127 (1993) 421
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Vekilov, P.G., Yu.G. Kuznetsov and A.A. Chernov, The effect of temperature on step motion; (101) ADP face 121 (1992) 44
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Vekilov, P.G. and Chr. Nanev, Elementary growth kinetics of silver electrocrystallization 125 (1992) 229
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Wang, H.S., D. Eissler, W. Dietsche, A. Fischer and K. Ploog, Molecular beam epitaxial growth and structural properties of $DyBa_2Cu_3O_{7-y}$ superconducting thin films 126 (1993) 565
Wang, H.S., D. Eissler, W. Dietsche, A. Fischer and K. Ploog, Investigation of MBE-grown high T_c films by RHEED, atomic force microscopy and X-ray diffraction 127 (1993) 655
Wang, J., A.U.H. Qureshi, Y.S. Tian, X. Wang, Y. Hu and S.D. Zheng, Hot wall epitaxial growth and characterization of diluted magnetic semiconductor $Zn_{1-x}Mn_xSe$ 126 (1993) 651
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Wang, M.L., Z.W. Shih and C.H. Lin, Reaction mechanism producing barium hexaferrites from goethite and barium hydroxide by hydrothermal method 130 (1993) 153
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Wang, X.L., A. Wakahara and A. Sasaki, OMVPE growth and characterization of $Al_xGa_{1-x}P$ $(0 \leqslant x \leqslant 1)$ using tertiarybutylphosphine 129 (1993) 289
Wang Yao-Shui, P. Bennema, Zheng Manna, C.M. Fu, C. Grey, L.W.M. Schreurs, Q. Xu, P. van der Linden and Y. Brynseraede, Improvement of superconductivity in YBCO single crystals 128 (1993) 744
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Wanklyn, B.M., E. Dieguez, Chen Changkang, A.K. Pradhan, J.W. Hodby, Hu Yongle, D. Smith, F. Wondre and P.A.J. de Groot, Improved thermogravimetric analysis and crystal growth of Bi–Sr–Ca–Cu–O 128 (1993) 738
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Ward, K.B., see Hannick 122 (1992) 303
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Watanabe, A., see Goto 127 (1993) 1005
Watanabe, A., T. Takeuchi, K. Hirosawa, H. Amano, K. Hiramatsu and I. Akasaki, The growth of single crystalline GaN on a Si substrate using AlN as an intermediate layer 128 (1993) 391
Watanabe, A., A. Tanaka and T. Sukegawa, GaSb solution growth by the solute feeding Czochralski method 128 (1993) 462
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Waters, K., A. Bensaoula, A. Schultz, K. Eipers-Smith and A. Freundlich, In-situ doping and composition monitoring for molecular beam epitaxy using mass spectroscopy of recoiled ions (MSRI) 127 (1993) 972
Watson, C.C.R. and K. Durose, Cathodoluminescence microscopy of bulk CdTe crystals 126 (1993) 325
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Wegerhoff, J. and G. Wagner, Crystal growth of plant calmodulin 122 (1992) 351
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W. Dondl and G. Abstreiter, Fabrication and properties of epitaxially stabilized Ge/α-Sn heterostructures on Ge(001) 123 (1992) 75
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Weidemann, G. and K. Jacobs, Thermodynamic analysis of metalorganic vapour phase epitaxy of $Hg_{1-x}Cd_xTe$ 125 (1992) 477
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Weisbuch, C., Applications of MBE-grown heterostructures and quantum wells in fundamental research and in advanced semiconductor devices 127 (1993) 742
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Wittgreffe, J.P., M.J. Yates, S.D. Perrin and P.C. Spurdens, Interface broadening in as-grown MOVPE InP/GaInAs MQW structures: dominant intermixing of group V elements directly revealed by Auger analysis of a chemically bevelled section 130 (1993) 51
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Wu, X., K.H. Gulden, M. Thomas, G. Wilson, J. Walker, G.H. Döhler, J.R. Whinnery and J.S. Smith, Selectively masked MBE regrowth 127 (1993) 896
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Xiao, Q. and J.J. Derby, The role of internal radiation and melt convection in Czochralski oxide growth: deep interfaces, interface inversion, and spiraling 128 (1993) 188
Xiao, Q. and J.J. Derby, Bulk-flow versus thermal-capillary models for Czochralski growth of semiconductors 129 (1993) 593
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Xu, Zhengyi, Chongru Huo, Peiwen Ge and Zhenhe Zhu, Analysis of the characteristics of crystal growth from solution under microgravity. II. Effects of various physical and geometrical parameters 125 (1992) 135
Xu, Zhengyi, Peiwen Ge, Chongru Huo and Zhenhe Zhu, Analyses of the characteristics of crystal growth from solution under microgravity. III. Effects of the orientation of microgravity 129 (1993) 506
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Yakusheva, N.A. and V.G. Pogadaev, Amphoteric behaviour of germanium during liquid phase epitaxy of GaAs from bismuth–gallium melts 123 (1992) 479
Yamada, C. and T. Kimura, Comments on "Optical second harmonic generation studies of the nature of the GaAs(100) surface in air" 130 (1993) 321
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Yamaguchi, H., M. Kasu, T. Sueyoshi, T. Sato and M. Iwatsuki, Observation of GaAs (001) surfaces at high temperatures by scanning tunneling microscopy 127 (1993) 1064
Yamaguchi, H. and Y. Horikoshi, Phase transition on III–V compound semiconductor surfaces observed by an improved RHEED technique 127 (1993) 976
Yamaguchi, Y., K. Yamagishi and Y. Nobe, The behavior of chromium ions in forsterite 128 (1993) 996
Yamamoto, J.K., K. Kitamura, N. Iyi and S. Kimura, Sc_2O_3-doped $LiNbO_3$ grown by the float zone method 121 (1992) 522
Yamamoto, J.K., S.A. Markgraf and A.S. Bhalla, $Sr_xBa_{1-x}Nb_2O_6$ single crystal fibers: dependence of crystal quality on growth parameters 123 (1992) 423
Yamamoto, J.K., K. Kitamura, N. Iyi, S. Kimura, Y. Furukawa and M. Sato, Growth and characterization of Sc_2O_3-doped $LiNbO_3$ 128 (1993) 920
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Yamamoto, T., M. Inai, T. Takebe, M. Fujii and K. Kobayashi, Periodic lateral structure of Al content modulations in AlGaAs grown on vicinal (111)A GaAs by molecular beam epitaxy 127 (1993) 865
Yamamoto, T., see Takebe 127 (1993) 937
Yamanaka, M., see Yase 121 (1992) 449
Yamanaka, M., K. Mimura, K. Yase, K. Sato and K. Inaoka, Growth mechanism of long chain molecular crystals on KCl substrate due to annealing 128 (1993) 113
Yamaoka S., M. Akaishi, H. Kanda and T. Osawa, Crystal growth of diamond in the system of carbon and water under very high pressure and temperature 125 (1992) 375
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Yanashima, K., K. Koyanagi, K. Hara, J. Yoshino and H. Kukimoto, MOVPE growth of p-type ZnSe using dimethylaminolithium as the dopant 124 (1992) 616
Yang Jianrong, Thermodynamic study of solid–vapour equilibrium in the $(Hg_{1-x}Cd_x)_{1-y}Te_y$ system 126 (1993) 695
Yang, J.R., C.K. Chung, W.J. Chen, Y.H. Chang and J. Hwang, Heteroepitaxy of PtSi/SiGe on Si(100) by dual electron gun co-deposition at high temperatures 121 (1992) 717

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Yano, M., H. Furuse, Y. Iwai, K. Yoh and M. Inoue, Raman scattering analysis of InAs/GaSb ultrathin-layer superlattices grown by molecular beam epitaxy 127 (1993) 807
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Yasuda, A., see Sugimoto 127 (1993) 1
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Yasuda, Y., K. Itoh, N. Ohshima, Y. Koide and S. Zaima, RHEED studies of initial stage of Ge film growth on (311)Si by gas source molecular beam epitaxy 128 (1993) 319
Yasui, K., T. Ido, H. Terada and S. Muto, LPE growth of $Bi_2Sr_2CaCu_2O_y$ from KCl solution 125 (1992) 653
Yates, H.M., J.O. Williams, I.L.J. Patterson and D.J. Cole-Hamilton, Preparation and purification of dimethylzinc and the effect of iodine doping on the opto-electronic properties of epitaxial ZnSe layers grown by metalorganic chemical vapour deposition 129 (1993) 215
Yates, M.J., M.R. Aylett, S.D. Perrin and P.C. Spurdens, Characterization of InP to GaInAs and GaInAs to InP interfaces using tilted cleaved corner TEM 124 (1992) 604
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Yen, C.T. and W.A. Tiller, Incorporating convection into one-dimensional solute redistribution during crystal growth from the melt. II. The initial transient solution 129 (1993) 224
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Yokotsuka, T., M.R. Wilby, D.D. Vvedensky, T. Kawamura, K. Fukutani and S. Ino, Incorporation and diffusion kinetics during epitaxial growth on Ge(111) 127 (1993) 479
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Yokoyama, E. and R.F. Sekerka, A numerical study of the combined effect of anisotropic surface tension and interface kinetics on pattern formation during the growth of two-dimensional crystals 125 (1992) 389
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Yonenaga, I. and K. Sumino, Behaviour of dislocations in GaAs revealed by etch pit technique and X-ray topography 126 (1993) 19
Yoneta, M., M. Ohishi, H. Saito and T. Hamasaki, Low temperature molecular beam epitaxial growth of ZnS/GaAs(001) by using elemental sulfur source 127 (1993) 314
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Zamerowski, J.H. Abeles, J.B. Kirk, J.T. McGinn and K.B. Murphy, MOCVD regrowth over GaAs/AlGaAs gratings for high power long-lived InGaAs/AlGaAs lasers 124 (1992) 709
Yoshida, H., see Fukatsu 127 (1993) 489
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Yoshikawa, N. and A. Kikuchi, Microstructure and growth rate of chemical vapour deposited TiN films in a vertical cold wall reactor 130 (1993) 578
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Yoshikawa, S., K. Shinzawa-Itoh, H. Ueda, T. Tsukihara, Y. Fukumoto, T. Kubota, M. Kawamoto, K. Fukuyama and H. Matsubara, Strategies for crystallization of large membrane protein complexes 122 (1992) 298
Yoshimoto, M., see Nagata 123 (1992) 1
Yoshimura, J. and S. Taki, Acicular crystals of synthetic quartz; a general view of their morphologies and defects 125 (1992) 237
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Yoshinaga, A., P. Mookherjee, R. Murray, J.H. Neave and B.A. Joyce, Surface relaxation kinetics and growth interruption effects in GaAs/AlAs single quantum wells 127 (1993) 788
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Yoshino, J., see Morii 124 (1992) 772
You, B.T., J.S. Shea, J.Y. Kao, J.R. Deng, Y.S. Chang, C.Y. Juan and T.P. Chen, Improvement of high brightness AlGaAs/GaAs DH red LED under optimum growth conditions 128 (1993) 527
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Young, Byung-Chun, Characterization of anatase type $(Sn_xTi_{1-x})O_2$ solid solutions grown by CVD 121 (1992) 148
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Yu, E.T., M.B. Johnson, V.P. Kesan, A.R. Powell, J.-M. Halbout and S.S. Iyer, Cross-sectional scanning tunneling microscopy of MBE-grown Si p–n junctions and Si/SiGe superlattices 127 (1993) 435
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Zaumseil, P., Characterization of the perfection of $Si_{1-x}Ga_x$ layers on silicon by X-ray methods 129 (1993) 537
Zayachuk, D.M., E.L. Matulenis and V.I. Mikityuk, The behaviour of Gd in lead and tin tellurides and its effect on their physical properties 121 (1992) 235
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Zeelen, J.Ph. and R.K. Wierenga, The growth of yeast thiolase crystals using a polyacrylamide gel as dialysis membrane 122 (1992) 194
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Zhang, G., A. Ovtchinnikov and M. Pessa, Role of growth temperature in GSMBE growth of strained-layer InGaAs/GaAs quantum well lasers 127 (1993) 209
Zhang, G., A. Ovtchinnikov, J. Näppi, T. Hakkarainen and H. Asonen, GSMBE growth of GaInAsP on GaAs substrates and its application to 0.98 μm lasers 127 (1993) 1033
Zhang, H., Y. Kamotani and S. Ostrach, Growth-in-gel zeolite crystallization and transport phenomena 128 (1993) 1288
Zhang, J., see Zhang 121 (1992) 381
Zhang, J. and G.H. Nancollas, Dissolution deceleration of calcium phosphate crystals at constant undersaturation 123 (1992) 59

Zhang, J., see Armstrong 124 (1992) 37
Zhang, J. and G.H. Nancollas, Interpretation of dissolution kinetics of dicalcium phosphate dihydrate 125 (1992) 251
Zhang, J., see Ohtani 127 (1993) 461
Zhang, J., see Shitara 127 (1993) 494
Zhang, J.H. and X.W. Fan, Surface process and lattice relaxation in growth of ZnS_xSe_{1-x} epilayers on GaAs substrate by VPE 121 (1992) 769
Zhang, K., see Burger 128 (1993) 1047
Zhang, L., J.Z. Liu, M.D. Lan, P. Klavins and R.N. Shelton, Crystal growth and superconductivity of $Bi_{1.7}Pb_{0.3}Sr_2CaCu_2O_8$ 128 (1993) 734
Zhang, Nan, Duo-rong Yuan, Xu-tang Tao, Zong-shu Shao, Shue-xing Dou, Min-hua Jiang and Dong Xu, New nonlinear optical crystal 3-methoxy-4-hydroxy-benzaldehyde and its phase-matched properties 123 (1992) 255
Zhang, W., Y. Someno, M. Sasaki and T. Hirai, Low-temperature epitaxial growth of AlN films on sapphire by electron cyclotron resonance plasma-assisted chemical vapor deposition 130 (1993) 308
Zhang, X., D.W. Pashley, J.H. Neave, J. Zhang and B.E. Joyce, A transmission electron microscopy (TEM) study of a wedge-shaped InAs epitaxial layer on GaAs (001) grown by molecular beam epitaxy (MBE) 121 (1992) 381
Zhang, X., see Zhou 127 (1993) 456
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Zhang, X.F., X.B. Zhang, G. Van Tendeloo, S. Amelinckx, M. Op de Beeck and J. Van Landuyt, Carbon nano-tubes; their formation process and observation by electron microscopy 130 (1993) 368
Zhang, Y.H., L. Tapfer, G.H. Lu and K. Ploog, Structural properties of $Ga_xIn_{1-x}As/Al_yIn_{1-y}As$ multiple layers grown on InP substrates by molecular beam epitaxy 127 (1993) 816
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Zhokhov, A.A. and G.A. Emel'chenko, Growth of $YBa_2Cu_3O_{7-\delta}$ single crystals on seeds by a modified top seeded solution growth (TSSG) technique 129 (1993) 786
Zhou, Cai-hua, see Wei 130 (1993) 447
Zhou, F., see Becker 125 (1992) 384
Zhou, G., X. Zhang, C. Sheng and X. Wang, An investigation on the thermal stability of the Ge_xSi_{1-x}/Si superlattice grown by MBE 127 (1993) 456
Zhou, J., M. Larrousse, W.R. Wilcox and L.L. Regel, Directional solidification with ACRT 128 (1993) 173
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Zhu Hongbin, see Pan 121 (1992) 141
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Zhu, W., J. Ahn, H.S. Tan and B.T. Tan, Crystal growth of diamond films synthesized by oxygen acetylene combustion flames 125 (1992) 649
Zhu, W., see Wang 129 (1993) 45
Zhu Weibing, see Wang 129 (1993) 774
Zhu, Zhenhe, see Xu 125 (1992) 135
Zhu, Zhenhe, see Xu 129 (1993) 506
Zilko, J.L., P.S. Davisson, L. Luther and K.D.C. Trapp, Improved compositional uniformity of InGaAsP grown by low pressure metalorganic vapor phase epitaxy using tertiary butyl phosphine as the phosphorus source 124 (1992) 112
Zimmermann, G., H. Protzmann, W. Stolz, E.O. Göbel, P. Gimmnich, A. Greiling, J. Lorberth, C. Thalmann and K. Rademann, In-situ formation of As–H functions by β-elimination of specific metalorganic arsenic compounds for the MOVPE of III/V semiconductors 124 (1992) 136
Zimmermann, G., H. Protzmann, T. Marschner, O. Zsebök, W. Stolz, E.O. Göbel, P. Gimmnich, J. Lorberth, T. Filz, P. Kurpas and W. Richter, Amino-arsine and -phosphine compounds for the MOVPE of III–V semiconductors 129 (1993) 37
Zimmermann, H., R. Boyn, C. Albers, K.W. Benz, D. Sinerius, C. Eiche, B.K. Meyer and D.M. Hoffmann, State and distribution of point defects in doped and undoped Bridgman-grown CdTe single crystals 128 (1993) 593
Zimmermann, H., U. Gösele, M. Seilenthal and P. Eichinger, Vacancy concentration wafer mapping in silicon 129 (1993) 582
Zinck, J.J., see Liu 123 (1992) 500
Zinck, J.J., see Liu 129 (1993) 111
Zipp, G.L. and N. Rodríguez-Hornedo, Phenytoin crystal growth rates in the presence of phosphate and chloride ions 123 (1992) 247
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